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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	66
Number of Gates	31000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k10atc100-3

The FLEX 10K architecture is similar to that of embedded gate arrays, the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. In addition, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays provide reduced die area and increased speed compared to standard gate arrays. However, embedded megafunctions typically cannot be customized, limiting the designer's options. In contrast, FLEX 10K devices are programmable, providing the designer with full control over embedded megafunctions and general logic while facilitating iterative design changes during debugging.

Each FLEX 10K device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), microcontroller, wide-data-path manipulation, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array: it is used to implement general logic, such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10K devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, EPC16, and EPC1441 configuration devices, which configure FLEX 10K devices via a serial data stream. Configuration data can also be downloaded from system RAM or from Altera's BitBlaster™ serial download cable or ByteBlasterMV™ parallel port download cable. After a FLEX 10K device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 320 ms, real-time changes can be made during system operation.

FLEX 10K devices contain an optimized interface that permits microprocessors to configure FLEX 10K devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10K device as memory and configure the device by writing to a virtual memory location, making it very easy for the designer to reconfigure the device.

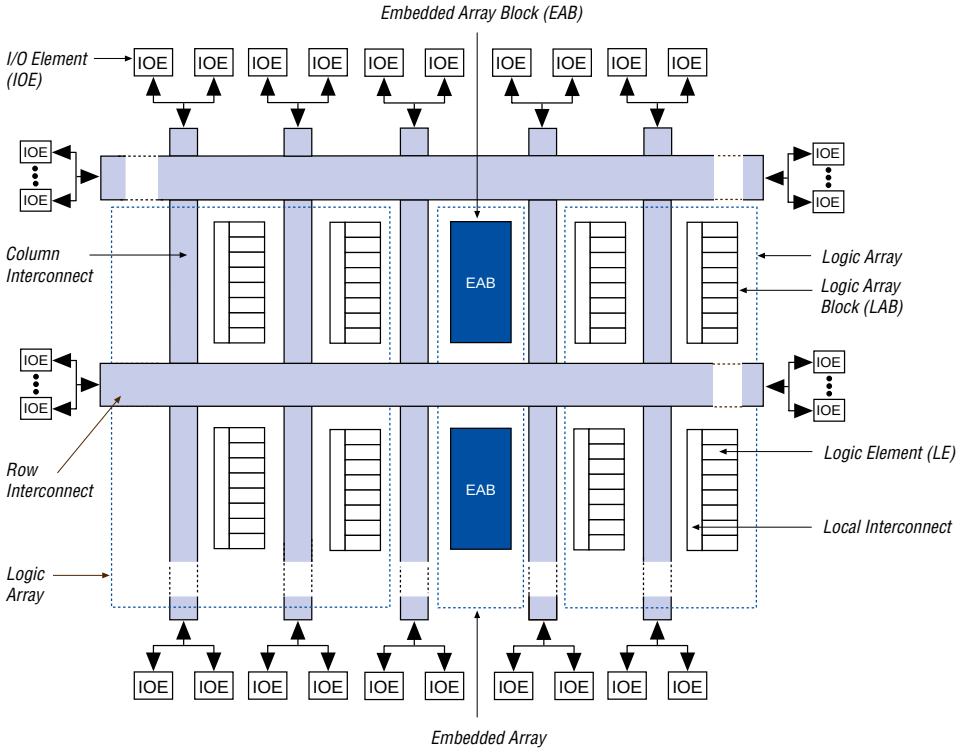
The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a 4-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10K devices and to and from device pins are provided by the FastTrack Interconnect, a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 1.6 ns and hold times of 0 ns; as outputs, these registers provide clock-to-output times as low as 5.3 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

Figure 1 shows a block diagram of the FLEX 10K architecture. Each group of LEs is combined into an LAB; LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect. IOEs are located at the end of each row and column of the FastTrack Interconnect.

Figure 1. FLEX 10K Device Block Diagram



FLEX 10K devices provide six dedicated inputs that drive the flipflops' control inputs to ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

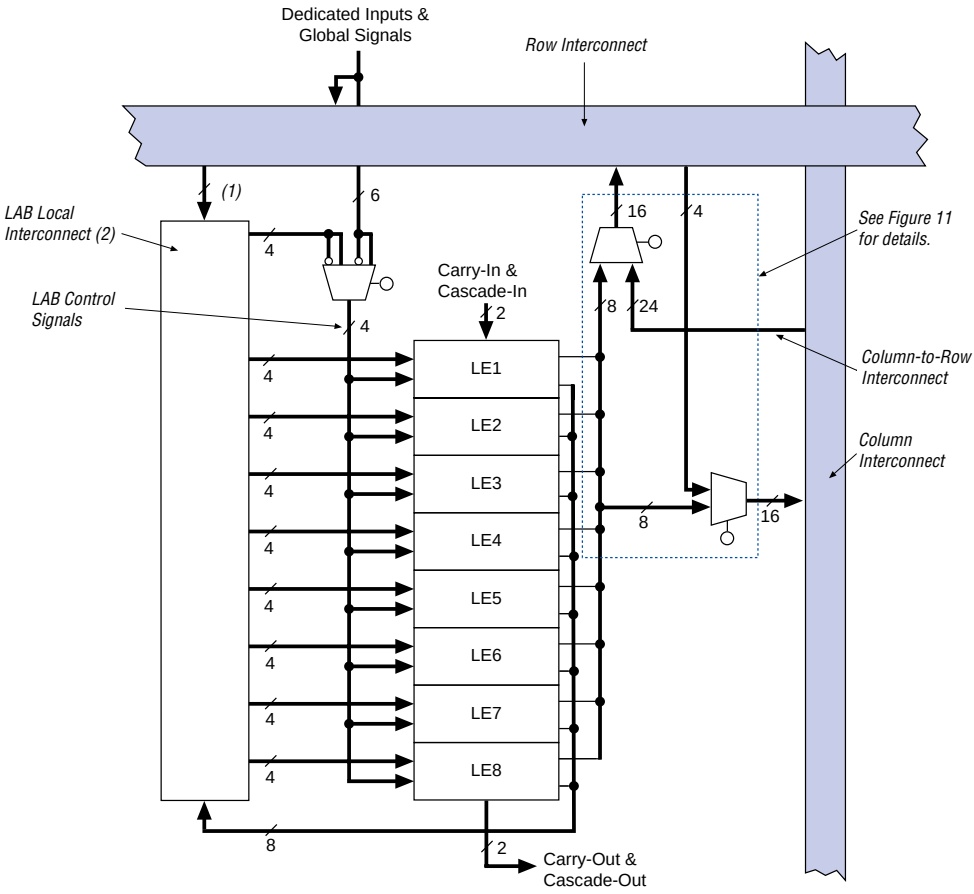
Embedded Array Block

The EAB is a flexible block of RAM with registers on the input and output ports, and is used to implement common gate array megafunctions. The EAB is also suitable for functions such as multipliers, vector scalars, and error correction circuits, because it is large and flexible. These functions can be combined in applications such as digital filters and microcontrollers.

Logic Array Block

Each LAB consists of eight LEs, their associated carry and cascade chains, LAB control signals, and the LAB local interconnect. The LAB provides the coarse-grained structure to the FLEX 10K architecture, facilitating efficient routing with optimum device utilization and high performance. See Figure 5.

Figure 5. FLEX 10K LAB

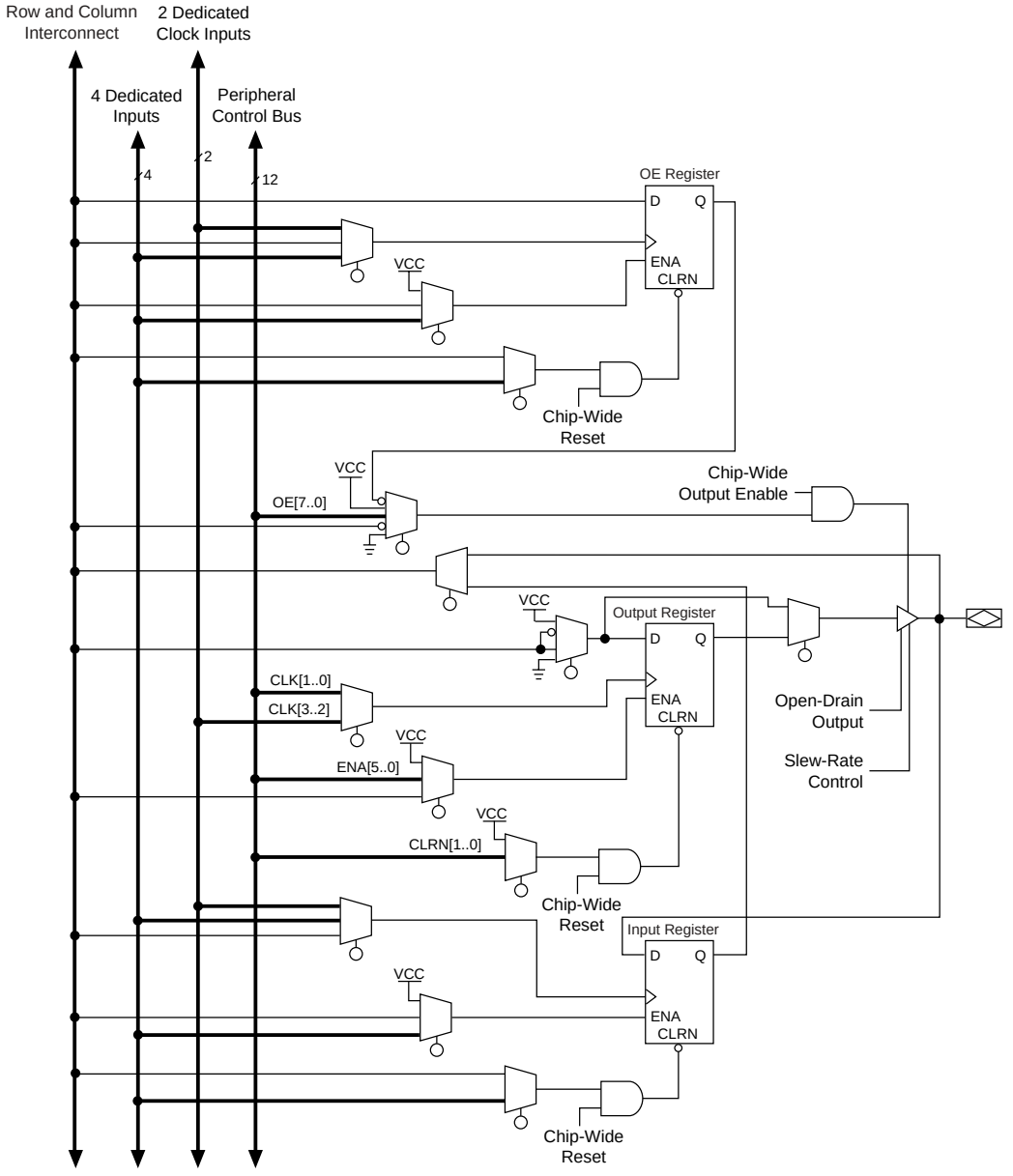


Notes:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

(2) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 30 LAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 34 LABs.

Figure 13. Bidirectional I/O Registers

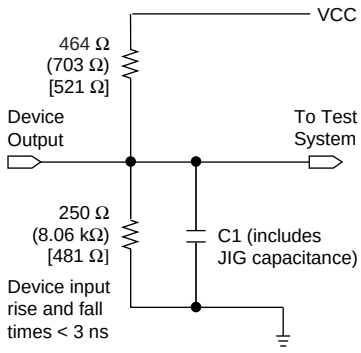


Generic Testing

Each FLEX 10K device is functionally tested. Complete testing of each configurable SRAM bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10K devices are made under conditions equivalent to those shown in Figure 19. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 19. FLEX 10K AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers without parentheses are for 5.0-V devices or outputs. Numbers in parentheses are for 3.3-V devices or outputs. Numbers in brackets are for 2.5-V devices or outputs.



Operating Conditions

Tables 17 through 21 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 5.0-V FLEX 10K devices.

Table 17. FLEX 10K 5.0-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–2.0	7.0	V
V_I	DC input voltage		–2.0	7.0	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		V_{CCINT} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 4.75 V *(7)*	2.4			V
	3.3-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 3.00 V *(7)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(7)*	V_{CCIO} – 0.2			V
V_{OL}	5.0-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 4.75 V *(8)*			0.45	V
	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(8)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(8)*			0.2	V
I_I	Input pin leakage current	V_I = V_{CC} or ground *(9)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = V_{CC} or ground *(9)*	–40		40	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

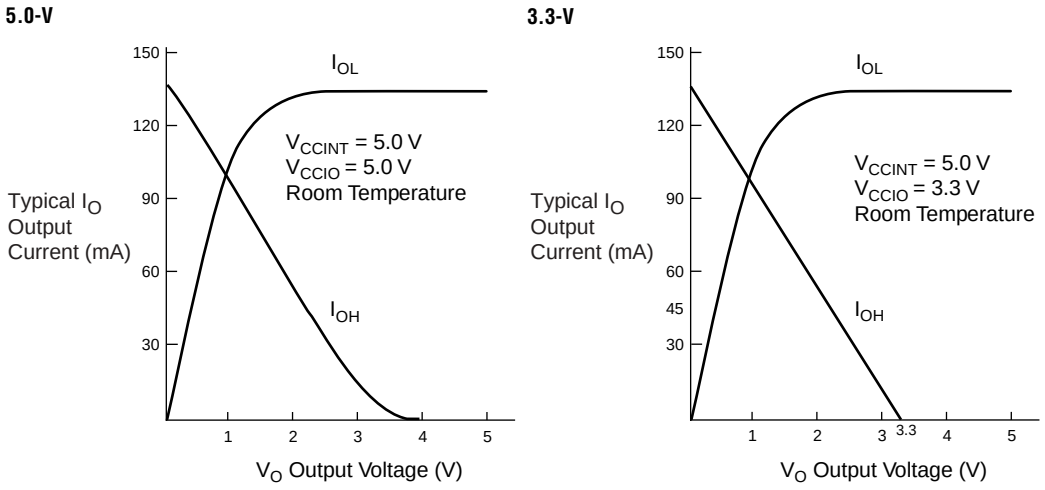
Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
(5) Typical values are for T_A = 25° C and V_{CC} = 5.0 V.
(6) These values are specified under the Recommended Operation Condition shown in Table 18 on page 45.
(7) The I_{OH} parameter refers to high-level TTL or CMOS output current.
(8) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(9) This value is specified for normal device operation. The value may vary during power-up.
(10) Capacitance is sample-tested only.

Figure 20 shows the typical output drive characteristics of FLEX 10K devices with 5.0-V and 3.3-V V_{CCIO}. The output driver is compliant with the 5.0-V ***PCI Local Bus Specification, Revision 2.2*** (for 5.0-V V_{CCIO}).

Figure 20. Output Drive Characteristics of FLEX 10K Devices



Timing simulation and delay prediction are available with the MAX+PLUS II Simulator and Timing Analyzer, or with industry-standard EDA tools. The Simulator offers both pre-synthesis functional simulation to evaluate logic design accuracy and post-synthesis timing simulation with 0.1-ns resolution. The Timing Analyzer provides point-to-point timing delay information, setup and hold time analysis, and device-wide performance analysis.

Figure 24 shows the overall timing model, which maps the possible paths to and from the various elements of the FLEX 10K device.

Figure 24. FLEX 10K Device Timing Model

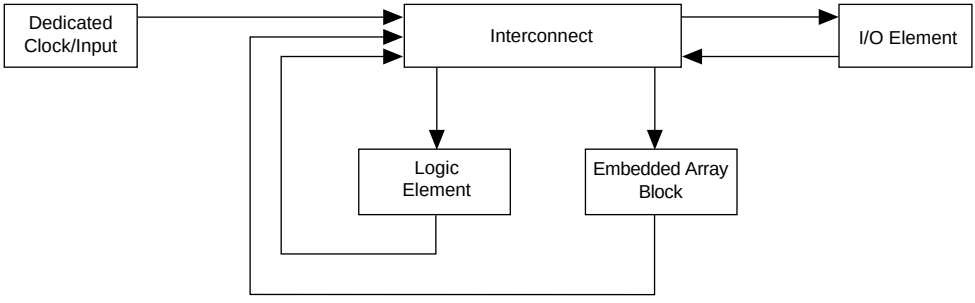
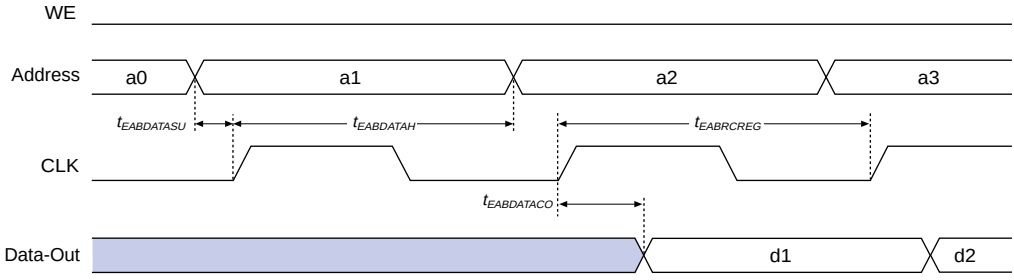


Figure 30. EAB Synchronous Timing Waveforms

EAB Synchronous Read



EAB Synchronous Write (EAB Output Registers Used)

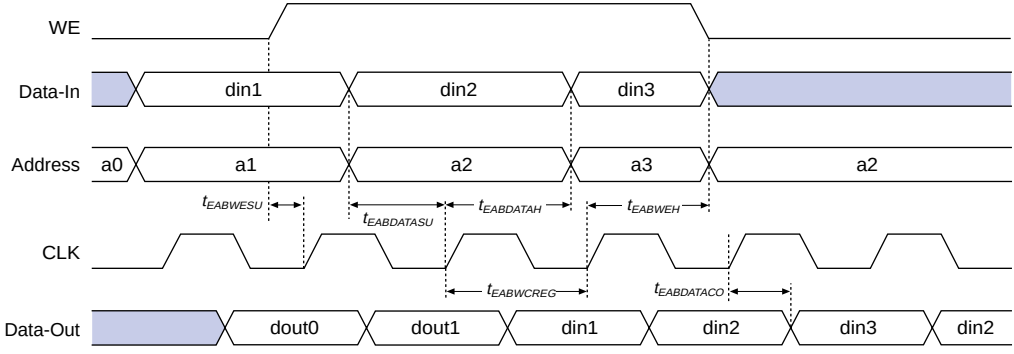


Table 43. EPF10K10 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		4.8		6.2	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		3.4		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.6		3.8	ns
$t_{SAMECOLUMN}$		0.9		1.1	ns
$t_{DIFFROW}$		4.5		4.9	ns
$t_{TWOROWS}$		8.1		8.7	ns
$t_{LEPERIPH}$		3.3		3.9	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 44. EPF10K20 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		5.2		6.6	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		4.3		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.7		3.9	ns
$t_{SAMECOLUMN}$		1.4		1.6	ns
$t_{DIFFROW}$		5.1		5.5	ns
$t_{TWOROWS}$		8.8		9.4	ns
$t_{LEPERIPH}$		4.7		5.6	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 49. EPF10K30, EPF10K40 & EPF10K50 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		0.4		0.6	ns
t_{IOC}		0.5		0.9	ns
t_{IOCO}		0.4		0.5	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	3.1		3.5		ns
t_{IOH}	1.0		1.9		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		3.3		3.6	ns
t_{OD2}		5.6		6.5	ns
t_{OD3}		7.0		8.3	ns
t_{XZ}		5.2		5.5	ns
t_{ZX1}		5.2		5.5	ns
t_{ZX2}		7.5		8.4	ns
t_{ZX3}		8.9		10.2	ns
t_{INREG}		7.7		10.0	ns
t_{IOFD}		3.3		4.0	ns
t_{INCOMB}		3.3		4.0	ns

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Tables 71 through 77 show EPF10K50V device internal and external timing parameters.

Table 71. EPF10K50V Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.3		1.6	ns
t_{CLUT}		0.1		0.5		0.6		0.6	ns
t_{RLUT}		0.5		0.8		0.9		1.0	ns
t_{PACKED}		0.4		0.4		0.5		0.7	ns
t_{EN}		0.7		0.9		1.1		1.4	ns
t_{CICO}		0.2		0.2		0.2		0.3	ns
t_{CGEN}		0.8		0.7		0.8		1.2	ns
t_{CGENR}		0.4		0.3		0.3		0.4	ns
t_{CASC}		0.7		0.7		0.8		0.9	ns
t_{C}		0.3		1.0		1.3		1.5	ns
t_{CO}		0.5		0.7		0.9		1.0	ns
t_{COMB}		0.4		0.4		0.5		0.6	ns
t_{SU}	0.8		1.6		2.2		2.5		ns
t_{H}	0.5		0.8		1.0		1.4		ns
t_{PRE}		0.8		0.4		0.5		0.5	ns
t_{CLR}		0.8		0.4		0.5		0.5	ns
t_{CH}	2.0		4.0		4.0		4.0		ns
t_{CL}	2.0		4.0		4.0		4.0		ns

Table 81. EPF10K130V Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		11.2		14.2		14.2	ns
$t_{EABRCCOMB}$	11.1		14.2		14.2		ns
$t_{EABRCREG}$	8.5		10.8		10.8		ns
t_{EABWP}	3.7		4.7		4.7		ns
$t_{EABWCCOMB}$	7.6		9.7		9.7		ns
$t_{EABWCREG}$	14.0		17.8		17.8		ns
t_{EABDD}		11.1		14.2		14.2	ns
$t_{EABDATACO}$		3.6		4.6		4.6	ns
$t_{EABDATASU}$	4.4		5.6		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		5.6		5.6		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	4.6		5.9		5.9		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.9		5.0		5.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		11.1		14.2		14.2	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 85 through 91 show EPF10K10A device internal and external timing parameters.

Table 85. EPF10K10A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.2		1.6	ns
t_{CLUT}		1.2		1.4		1.9	ns
t_{RLUT}		1.9		2.3		3.0	ns
t_{PACKED}		0.6		0.7		0.9	ns
t_{EN}		0.5		0.6		0.8	ns
t_{CICO}		02		0.3		0.4	ns
t_{CGEN}		0.7		0.9		1.1	ns
t_{CGENR}		0.7		0.9		1.1	ns
t_{CASC}		1.0		1.2		1.7	ns
t_{C}		1.2		1.4		1.9	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	1.1		1.3		1.7		ns
t_{H}	0.6		0.7		0.9		ns
t_{PRE}		0.5		0.6		0.9	ns
t_{CLR}		0.5		0.6		0.9	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 86. EPF10K10A Device IOE Timing Microparameters *Note (1)* **(Part 1 of 2)**

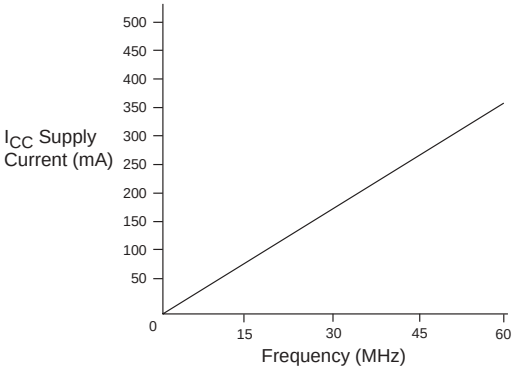
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
		1.3		1.5		2.0	ns
t_{IOC}		0.2		0.3		0.3	ns
t_{IOCO}		0.2		0.3		0.4	ns
t_{IOCOMB}		0.6		0.7		0.9	ns
t_{IOSU}	0.8		1.0		1.3		ns

Table 101. EPF10K100A Device EAB Internal Microparameters *Note (1)*

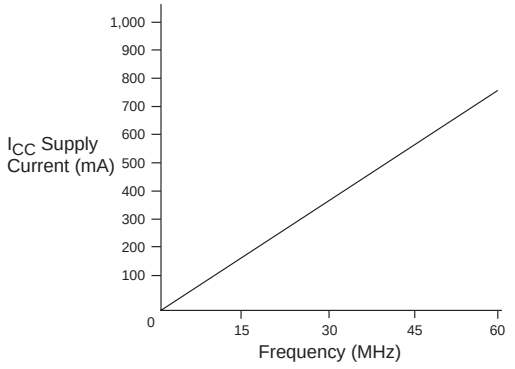
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.8		2.1		2.4	ns
$t_{EABDATA2}$		3.2		3.7		4.4	ns
t_{EABWE1}		0.8		0.9		1.1	ns
t_{EABWE2}		2.3		2.7		3.1	ns
t_{EABCLK}		0.8		0.9		1.1	ns
t_{EABCO}		1.0		1.1		1.4	ns
$t_{EABBYPASS}$		0.3		0.3		0.4	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	0.4		0.5		0.5		ns
t_{AA}		4.1		4.8		5.6	ns
t_{WP}	3.2		3.7		4.4		ns
t_{WDSU}	2.4		2.8		3.3		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	0.2		0.2		0.3		ns
t_{WAH}	0.0		0.0		0.0		ns
t_{WO}		3.4		3.9		4.6	ns
t_{DD}		3.4		3.9		4.6	ns
t_{EABOUT}		0.3		0.3		0.4	ns
t_{EABCH}	2.5		3.5		4.0		ns
t_{EABCL}	3.2		3.7		4.4		ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)

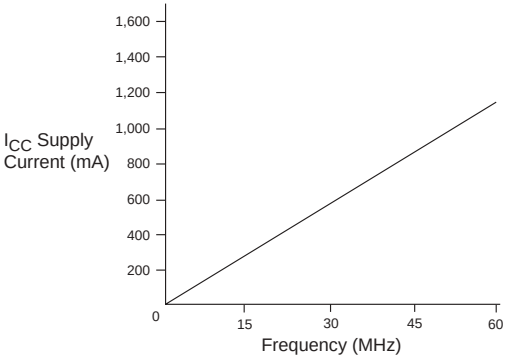
EPF10K10



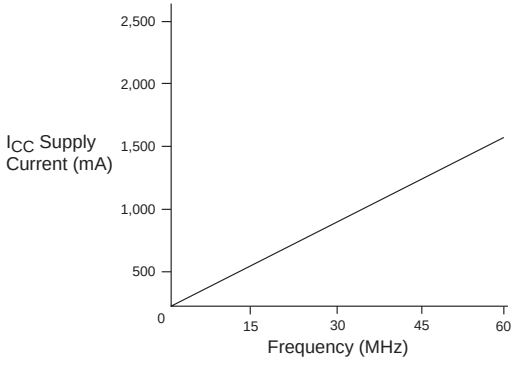
EPF10K20



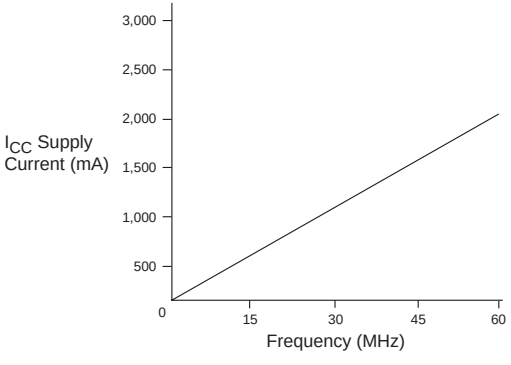
EPF10K30



EPF10K40



EPF10K50



EPF10K70

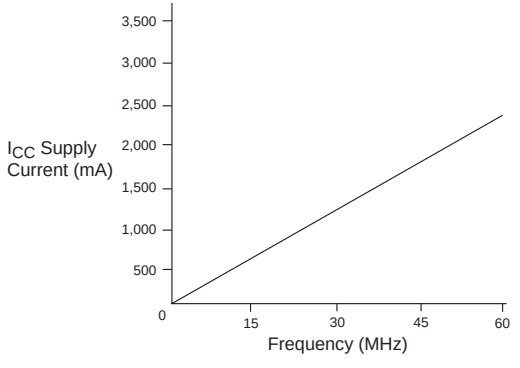
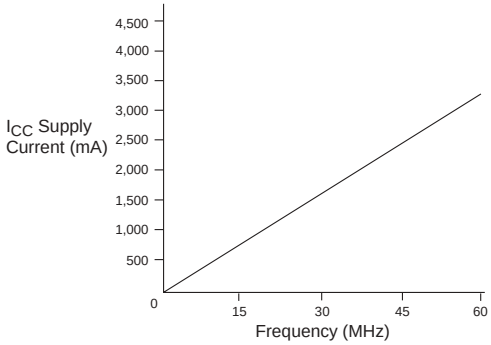
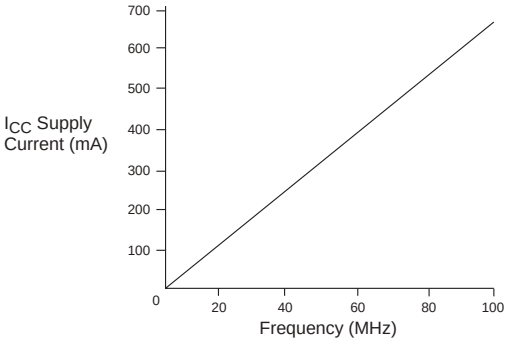


Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 2 of 3)

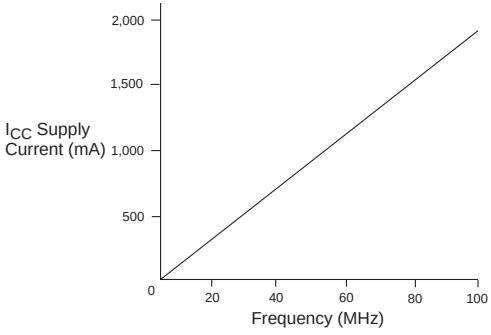
EPF10K100



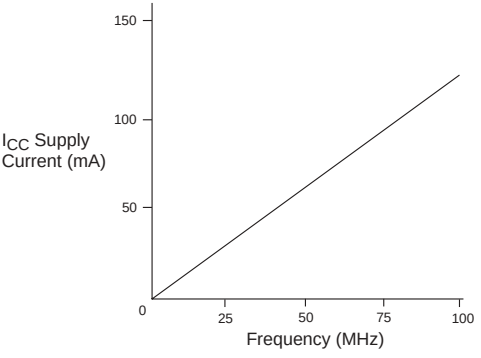
EPF10K50V



EPF10K130V



EPF10K10A



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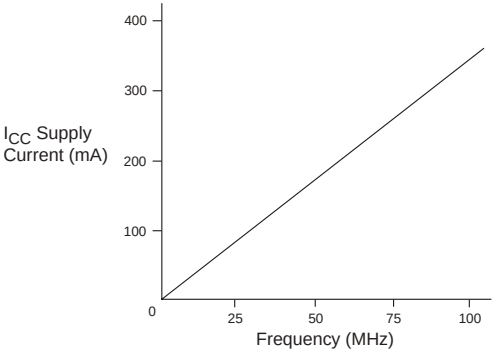
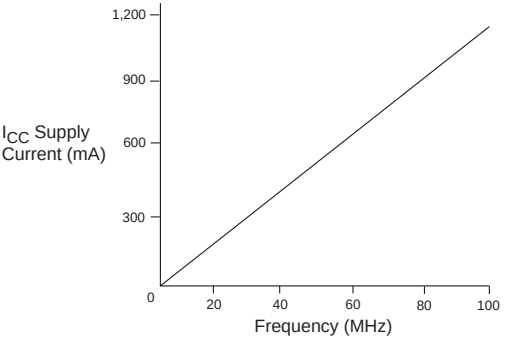


EPF10K100A



101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
http://www.altera.com
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com

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